

IN THE SPECIFICATION:

Please amend paragraph 31 as follows:

[31] FIG. 2A shows a process of manufacturing a metallic film consisting of such as Pt, Au, Cu, Al, Ni, Ag, Ir, Pd, Ti, Ru, Ta, W, Os, or Rh, comprising giant single crystal grains according to one embodiment of the present invention.

Please amend paragraph 32 as follows:

[32] Referring to FIG. 2A, a metallic film 201 for driving a electronic device or processing a signal is deposited on a substrate 200. The deposition process is executed under an atmosphere comprising an inert gas, i.e., argon, and a desired additive gas such as O₂, N₂+O₂, N₂O, Cl, or N₂ to change surface energy, grain boundary energy or internal strain energy of the metallic film.

Please amend paragraph 43 as follows:

[34] FIG. 3B shows a device fabricated on the metallic film consisting of a giant single crystal grains produced according to the present invention using the patterning technique, specifically a shadow mask.